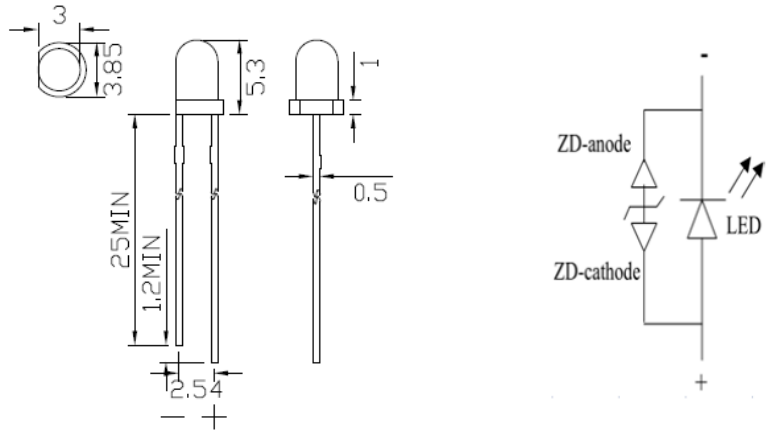




1. Features:

Lighting Color: White
Lens Color: Water Clear

2. (Package Dimensions):



3. Electrical Optical Characteristics (Ta = 25°C):

Parameter	Symbol	Min	Type	Max	Unit	Test Condition
Luminous Intensity	IV	9000	--	15000	mcd	IF=20mA
Color Temperature	T	8000	--	10000	K	IF=20mA
Forward Voltage	VF	2.9	--	3.1	V	IF=20mA
Reverse Current	IR			5	uA	VR=5V
Viewing Angle	2θ1/2	--	30	--	deg	IF=20mA

Notes:
 Absolute maximum ratings Ta=25°C
 Tolerance of measurements of forward voltage ± 0.2V
 Tolerance of measurements of peak Wavelength ± 2.0nm
 Tolerance of measurements of luminous intensity ± 15%
 Electrostatic sensitive device when handling, please use anti-electrostatic gloves.
 Please do not apply stress to the resin at high temperature
 Color bin grading is available for special applications.

4. Absolute Maximum Ratings (Ta=25°C):

Parameter	(Rating)	(Unit)
Reverse Voltage	5	V
Power Dissipation, Per Dice	100	mW/chip
Operating Temperature Ranger	-40 ~ +85	°C
Storage Humidity	45% ~85%	RH
Storage Temperature Ranger	-40~+100	°C
Soldering Temperature	260°C for 5 Seconds	
Peak IF(ma) (1/10Duty Cycle 0.1ms)	100	mA/chip
Pulse Width		
Continuous Forward Current	30	mA/chip

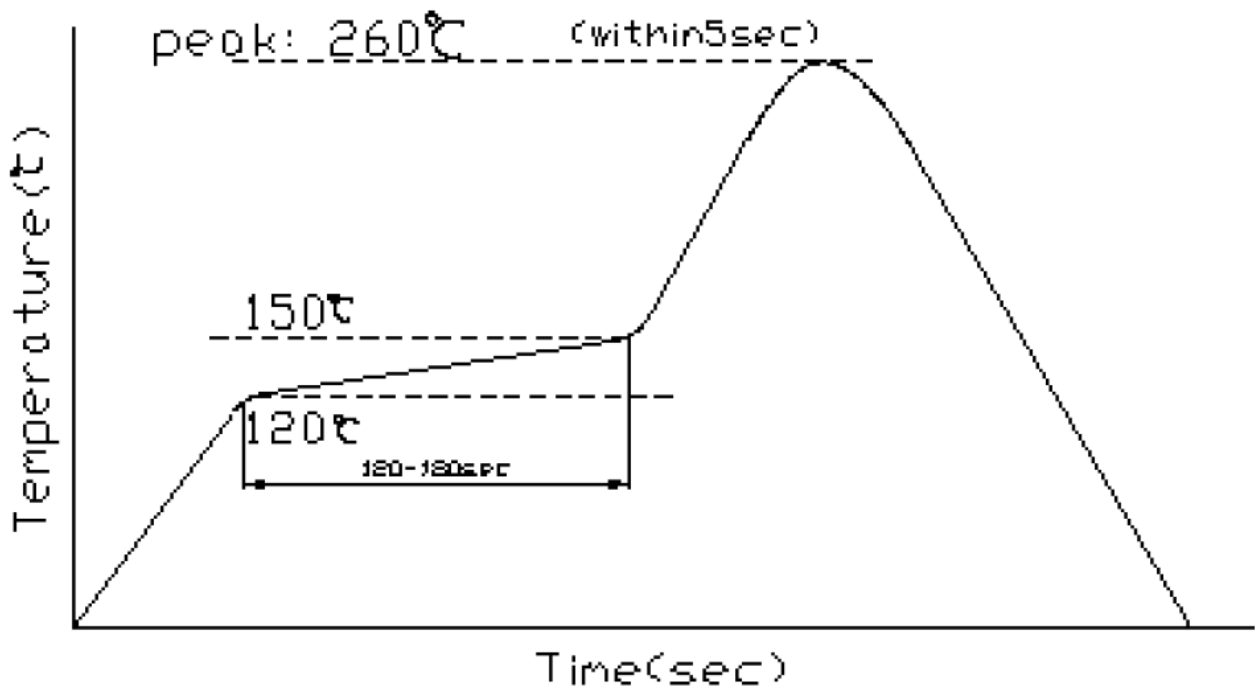


SE-34SWC-Z
LED 3mm, weiß mit Z-Diode

5. (Reliability Performance):

Test Classification	Test Item	Test Condition	Test Duration	Sample QTY	AC/RE
Life Test	Room Temperature DC Operating Life Test	Ta=25°C ± 5°C, IF=20mA	1000hrs	30pcs	0/1
	Thermal Shock Test	-10°C ± 5°C ←→ +100°C ± 5°C 5min. 10sec. 5min.	50 cycles	30pcs	0/1
Environment Test	Temperature Cycle Test	-40°C ± 5°C ←→ +25°C ± 5°C ←→ +85°C ± 5°C 30min. 5min. 30min.	50 cycles	30pcs	0/1
	High Temperature & High Humidity Test	Ta=85°C ± 5°C RH= 85%±0.5 % RH	1000hrs	30pcs	0/1
	High Temperature Storage	Ta=100°C ± 5°C	1000hrs	30pcs	0/1
	Low Temperature Storage	Ta=-55°C ± 5°C	1000hrs	30pcs	0/1
Mechanical Test	Resistance to Soldering Heat	Ta=230°C ± 5°C	5 sec.	30pcs	0/1
	Lens Integrity	Load 2.5N (0.25kgf) 0° ~ 90° ~ 0°	3 times	30pcs	0/1

6. (Recommended Wave Soldering Profiles):



7. Bin Code:

BIN NO.	IV	CCT	VF
BIN 1-1-1	9000-12000MCD	8000-8600K	2.9-3.1V
BIN 1-2-1	9000-12000MCD	8600-9300K	2.9-3.1V
BIN 1-3-1	9000-12000MCD	9300-10000K	2.9-3.1V
BIN 2-1-1	12000-15000MCD	8000-8600K	2.9-3.1V
BIN 2-2-1	12000-15000MCD	8600-9300K	2.9-3.1V
BIN 2-3-1	12000-15000MCD	9300-10000K	2.9-3.1V

8. Including Si Zener-diode Chip

1. Scope

- The specification applies to planar Zener diode.
- Extra lower leakage current
- Special thickness for special assembly process.

2. Structure

- Planar type Zener diode
- Electrode P (anode) :Aluminum (Gold for option)
- Electrode N (cathode) side: Gold.

3. Size

- Chip size : 8.0mil x 8.0mil \pm 0.8mil (0.2032 x 0.2032mm \pm 0.020mm)
- Thickness : 4.0mil / 6.0mil \pm 0.6mil (0.110mm / 0.152mm \pm 0.015mm)
- Pad Size : 6.0mil x 6.0mil \pm 0.4mil (0.152mm x 0.152mm \pm 0.010mm)
- Pattern drawing : per fig. 1

4. Electrical Characteristics (Ta =+25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	Rank A: $I_F = 10\text{mA}$	3		5	V
Forward Leakage current	I_F	Rank A: $V_F = 2.5\text{V}$			500	nA
Reverse Voltage	V_Z	Rank A: $I_R = 10\text{mA}$	3.5		6	V
Reverse Leakage current	I_R	Rank A: $V_R = 3\text{V}$			500	nA

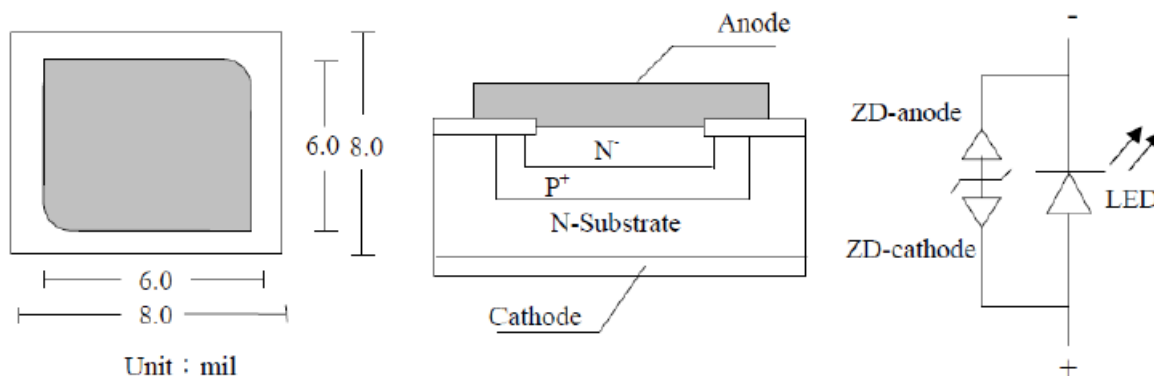


fig. 1